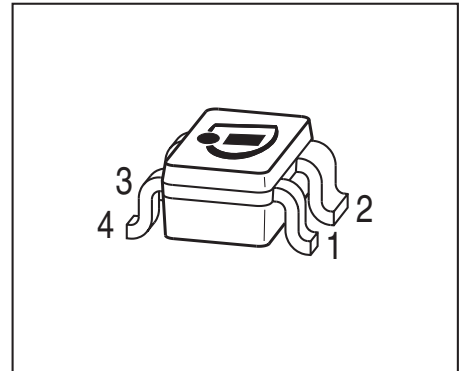


**NPN Silicon RF Transistor**

- For high gain low noise amplifiers
- For oscillators up to 10 GHz
- Noise figure  $F = 1.1$  dB at 1.8 GHz  
outstanding  $G_{ms} = 21$  dB at 1.8 GHz
- Transition frequency  $f_T = 25$  GHz
- Gold metallization for high reliability
- SIEGET<sup>®</sup> 25 GHz ft - Line
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration						Package
BFP420	AMs	1=B	2=E	3=C	4=E	-	-	SOT343

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$		V
$T_A > 0$ °C		4.5	
$T_A \leq 0$ °C		4.1	
Collector-emitter voltage	$V_{CES}$	15	
Collector-base voltage	$V_{CBO}$	15	
Emitter-base voltage	$V_{EBO}$	1.5	
Collector current	$I_C$	35	mA
Base current	$I_B$	3	
Total power dissipation <sup>2)</sup>	$P_{tot}$	160	mW
$T_S \leq 107$ °C			
Junction temperature	$T_j$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{stg}$	-65 ... 150	

<sup>1)</sup>Pb-containing package may be available upon special request

<sup>2)</sup> $T_S$  is measured on the collector lead at the soldering point to the pcb

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 260$	K/W

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics**

Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4.5	5	-	V
Collector-emitter cutoff current $V_{CE} = 15 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	10	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 5 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 0.5 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	3	$\mu\text{A}$
DC current gain $I_C = 20 \text{ mA}, V_{CE} = 4 \text{ V}$ , pulse measured	$h_{FE}$	60	95	130	-

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics (verified by random sampling)</b>					
Transition frequency $I_C = 30\text{ mA}$ , $V_{CE} = 3\text{ V}$ , $f = 2\text{ GHz}$	$f_T$	18	25	-	GHz
Collector-base capacitance $V_{CB} = 2\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , emitter grounded	$C_{cb}$	-	0.15	0.3	pF
Collector emitter capacitance $V_{CE} = 2\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , base grounded	$C_{ce}$	-	0.37	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$ , $V_{CB} = 0$ , collector grounded	$C_{eb}$	-	0.55	-	
Noise figure $I_C = 5\text{ mA}$ , $V_{CE} = 2\text{ V}$ , $f = 1.8\text{ GHz}$ , $Z_S = Z_{Sopt}$	$F$	-	1.1	-	dB
Power gain, maximum stable <sup>1)</sup> $I_C = 20\text{ mA}$ , $V_{CE} = 2\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 1.8\text{ GHz}$	$G_{ms}$	-	21	-	dB
Insertion power gain $V_{CE} = 2\text{ V}$ , $I_C = 20\text{ mA}$ , $f = 1.8\text{ GHz}$ , $Z_S = Z_L = 50\ \Omega$	$ S_{21} ^2$	14	17	-	
Third order intercept point at output <sup>2)</sup> $V_{CE} = 2\text{ V}$ , $I_C = 20\text{ mA}$ , $f = 1.8\text{ GHz}$ , $Z_S = Z_L = 50\ \Omega$	$IP_3$	-	22	-	dBm
1dB Compression point at output $I_C = 20\text{ mA}$ , $V_{CE} = 2\text{ V}$ , $Z_S = Z_L = 50\ \Omega$ , $f = 1.8\text{ GHz}$	$P_{-1dB}$	-	12	-	

$$^1G_{ms} = |S_{21} / S_{12}|$$

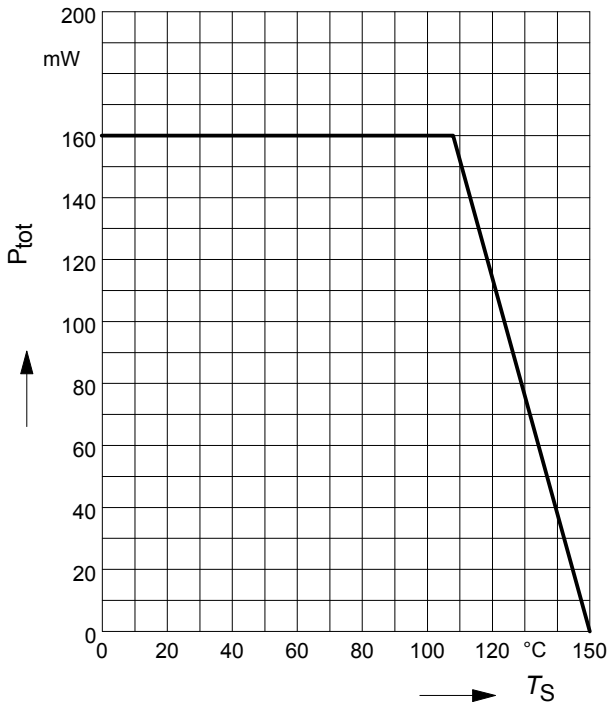
<sup>2</sup>IP3 value depends on termination of all intermodulation frequency components.  
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

**Simulation Data**

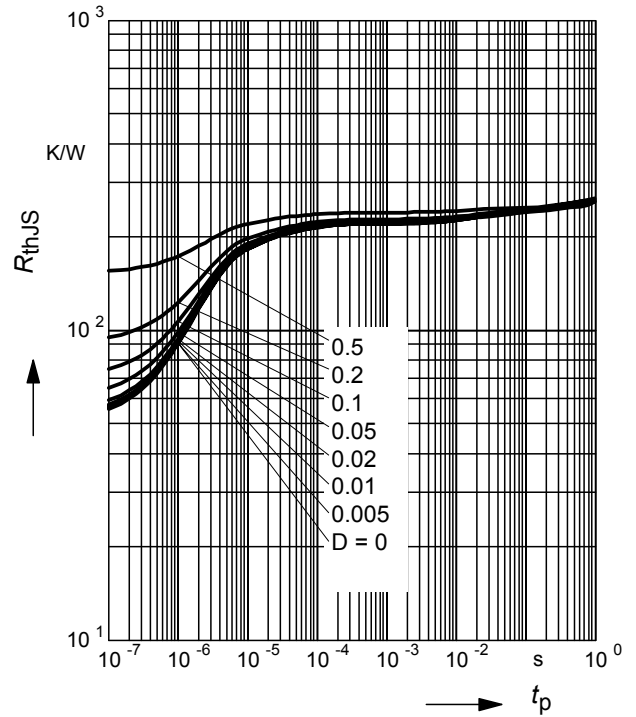
For SPICE-model as well as for S-parameters including noise parameters refer to our internet website: [www.infineon.com/rf.models](http://www.infineon.com/rf.models). Please consult our website and download the latest version before actually starting your design.

The simulation data have been generated and verified up to 10 GHz using typical devices. The BFP420 nonlinear SPICE-model reflects the typical DC- and RF-device performance with high accuracy.

**Total power dissipation  $P_{tot} = f(T_S)$**

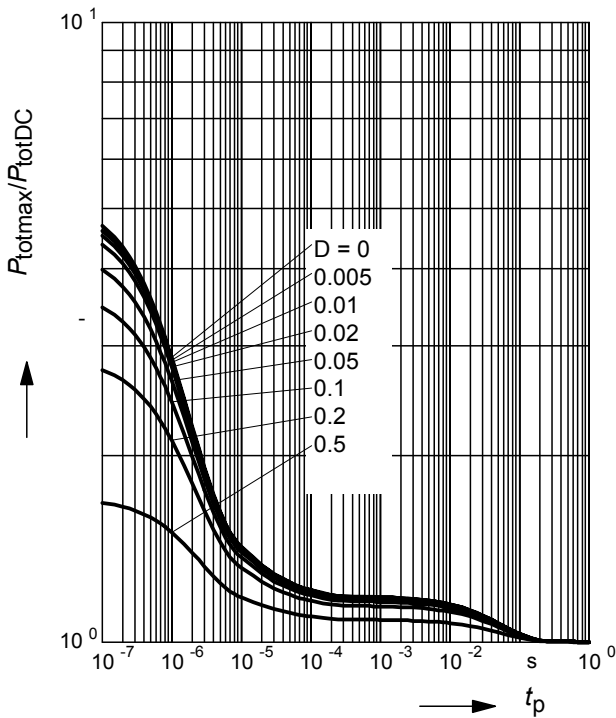


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



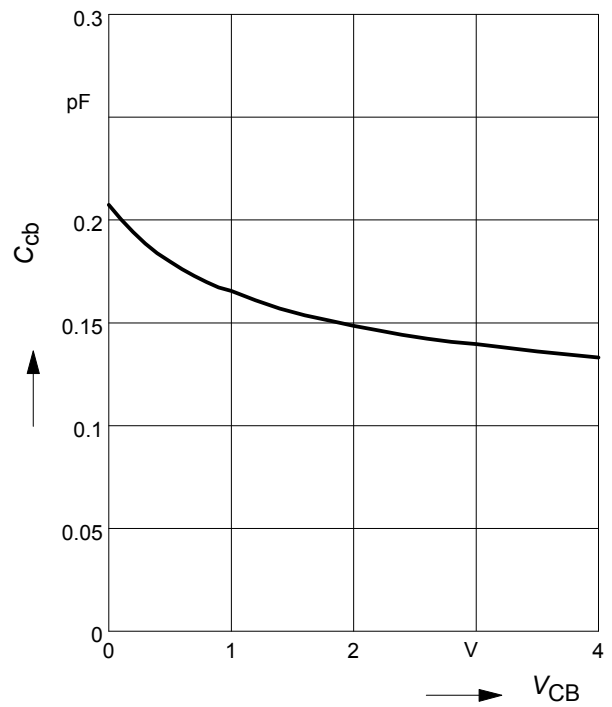
**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$



**Collector-base capacitance  $C_{cb} = f(V_{CB})$**

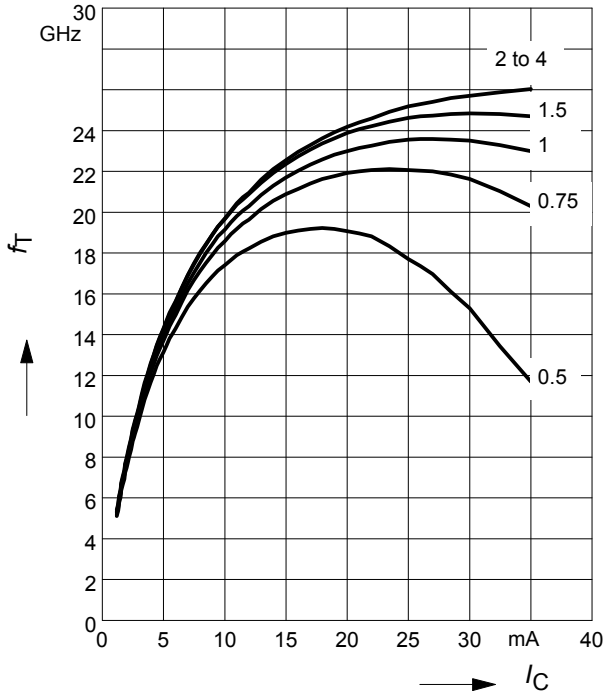
$f = 1\text{MHz}$



Transition frequency  $f_T = f(I_C)$

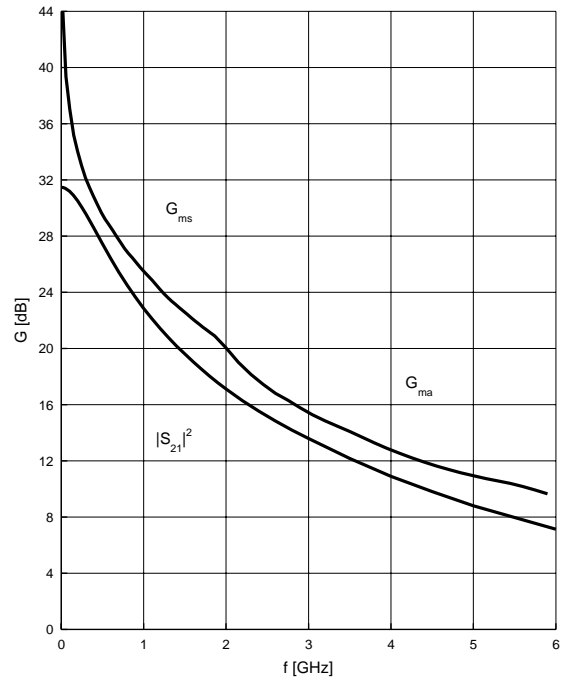
$f = 2 \text{ GHz}$

$V_{CE} = \text{parameter in V}$



Power gain  $G_{ma}, G_{ms}, |S_{21}|^2 = f(f)$

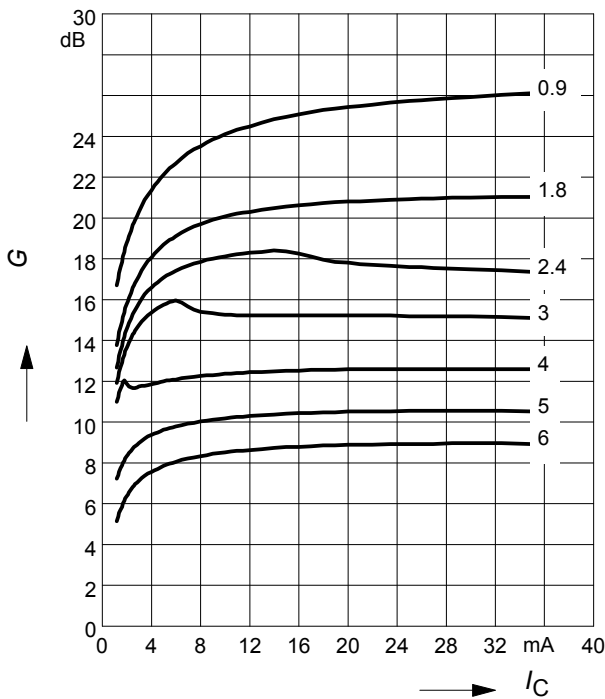
$V_{CE} = 2 \text{ V}, I_C = 20 \text{ mA}$



Power gain  $G_{ma}, G_{ms} = f(I_C)$

$V_{CE} = 2 \text{ V}$

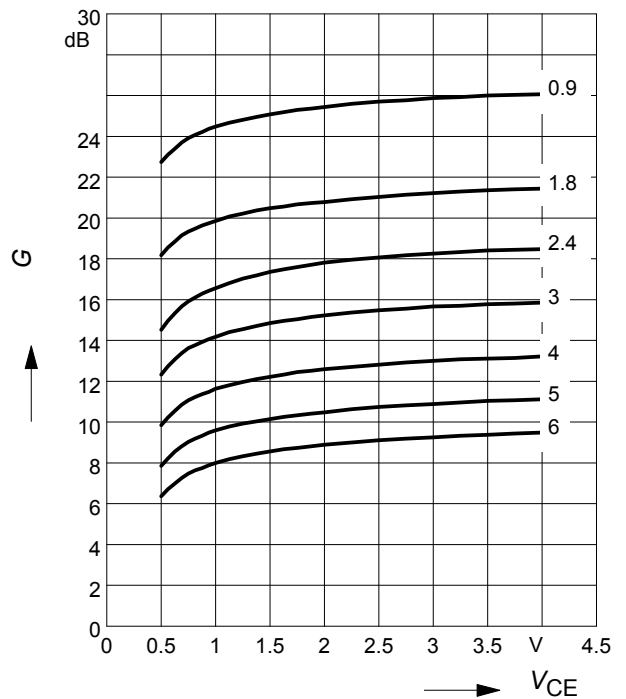
$f = \text{parameter in GHz}$



Power gain  $G_{ma}, G_{ms} = f(V_{CE})$

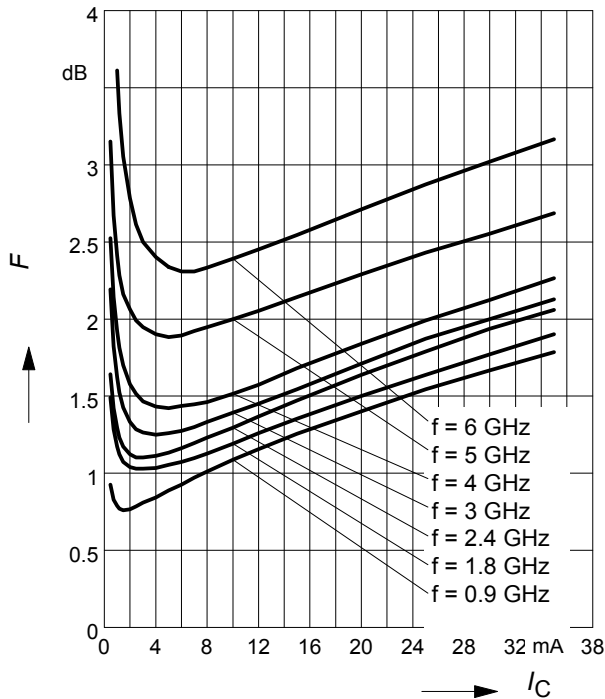
$I_C = 20 \text{ mA}$

$f = \text{parameter in GHz}$



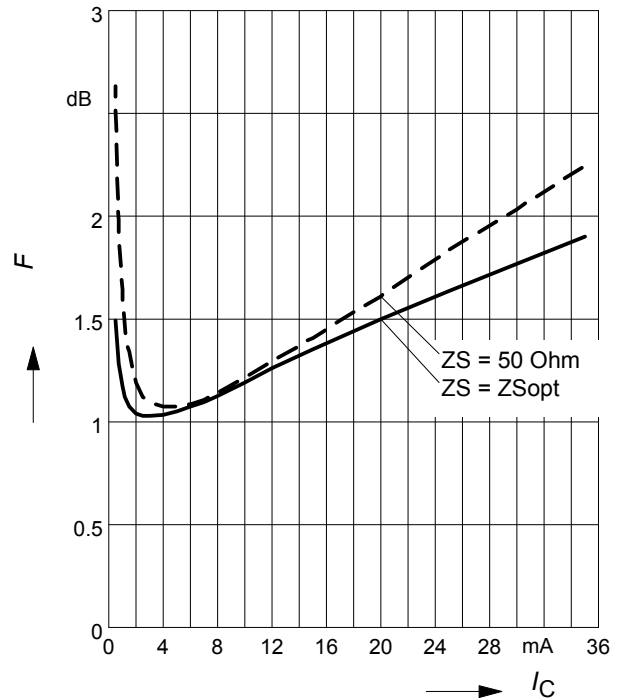
**Noise figure  $F = f(I_C)$**

$V_{CE} = 2\text{ V}$ ,  $Z_S = Z_{Sopt}$



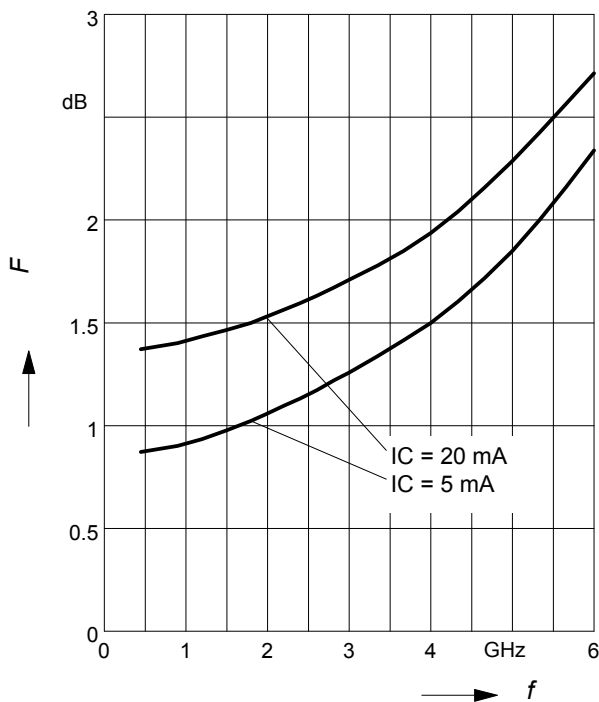
**Noise figure  $F = f(I_C)$**

$V_{CE} = 2\text{ V}$ ,  $f = 1.8\text{ GHz}$



**Noise figure  $F = f(f)$**

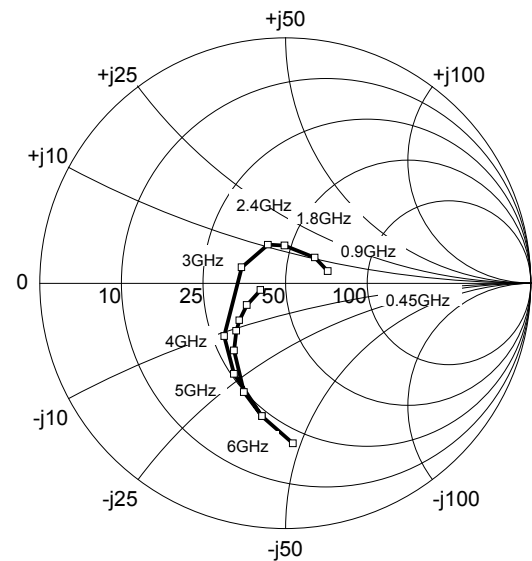
$V_{CE} = 2\text{ V}$ ,  $Z_S = Z_{Sopt}$



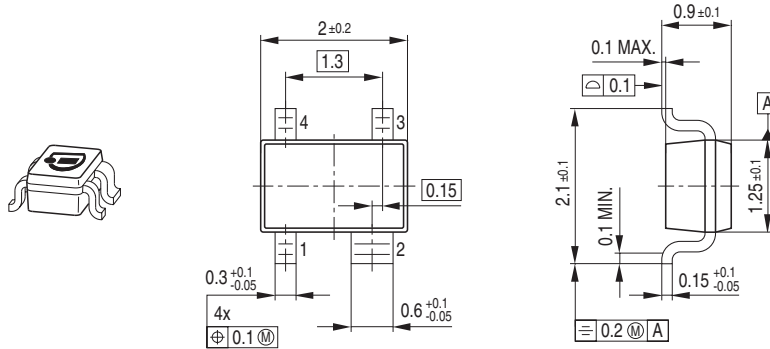
**Source impedance for min.**

noise figure vs. frequency

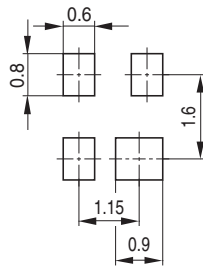
$V_{CE} = 2\text{ V}$ ,  $I_C = 5\text{ mA} / 20\text{ mA}$



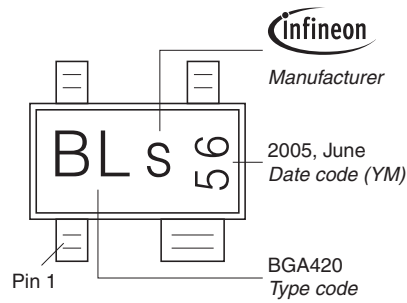
Package Outline



Foot Print

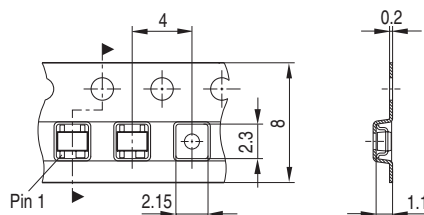


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel





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